

TOSHIBA Field Effect Transistor Silicon P-Channel MOS Type

SSM3J108TU

High Speed Switching Applications

- 1.8V drive
- Low on-resistance: $R_{on} = 363\text{m}\Omega$ (max) (@ $V_{GS} = -1.8\text{ V}$)
 $R_{on} = 230\text{m}\Omega$ (max) (@ $V_{GS} = -2.5\text{ V}$)
 $R_{on} = 158\text{m}\Omega$ (max) (@ $V_{GS} = -4.0\text{ V}$)

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Rating	Unit
Drain-Source voltage	V_{DS}	-20	V
Gate-Source voltage	V_{GSS}	± 8	V
Drain current	DC	I_D	A
	Pulse	I_{DP}	
Drain power dissipation	P_D (Note 1)	800	mW
	P_D (Note 2)	500	
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55~150	$^\circ\text{C}$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Mounted on ceramic board.
(25.4 mm $\times$ 25.4 mm $\times$ 0.8 mm, Cu Pad: 645 mm²)

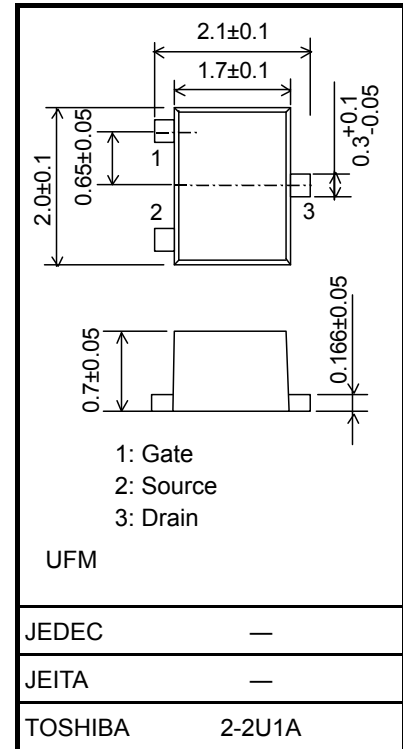
Note 2: Mounted on FR4 board.
(25.4 mm $\times$ 25.4 mm $\times$ 1.6 mm, Cu Pad: 645 mm²)

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Test Conditions	Min	Typ.	Max	Unit
Drain-Source breakdown voltage	$V_{(BR)DSS}$	$I_D = -1\text{ mA}$, $V_{GS} = 0$	-20	—	—	V
	$V_{(BR)DSX}$	$I_D = -1\text{ mA}$, $V_{GS} = +8\text{ V}$	-12	—	—	
Drain cut-off current	I_{DSS}	$V_{DS} = -20\text{ V}$, $V_{GS} = 0$	—	—	-10	μA
Gate leakage current	I_{GSS}	$V_{GS} = \pm 8\text{ V}$, $V_{DS} = 0$	—	—	± 1	μA
Gate threshold voltage	V_{th}	$V_{DS} = -3\text{ V}$, $I_D = -1\text{ mA}$	-0.3	—	-1.0	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = -3\text{ V}$, $I_D = -0.8\text{ A}$ (Note3)	1.9	3.2	—	S
Drain-Source on-resistance	$R_{DS(ON)}$	$I_D = -0.8\text{ A}$, $V_{GS} = -4.0\text{ V}$ (Note3)	—	125	158	m Ω
		$I_D = -0.4\text{ A}$, $V_{GS} = -2.5\text{ V}$ (Note3)	—	170	230	
		$I_D = -0.1\text{ A}$, $V_{GS} = -1.8\text{ V}$ (Note3)	—	230	363	
Input capacitance	C_{iss}	$V_{DS} = -10\text{ V}$, $V_{GS} = 0$, $f = 1\text{ MHz}$	—	250	—	pF
Output capacitance	C_{oss}	$V_{DS} = -10\text{ V}$, $V_{GS} = 0$, $f = 1\text{ MHz}$	—	45	—	pF
Reverse transfer capacitance	C_{rss}	$V_{DS} = -10\text{ V}$, $V_{GS} = 0$, $f = 1\text{ MHz}$	—	35	—	pF
Switching time	Turn-on time	$V_{DD} = -10\text{ V}$, $I_D = -0.25\text{ A}$, $V_{GS} = 0 \sim -2.5\text{ V}$, $R_G = 4.7\text{ }\Omega$	—	12	—	ns
	Turn-off time		—	18	—	
Drain-Source forward voltage	V_{DSF}	$I_D = 1.8\text{ A}$, $V_{GS} = 0\text{ V}$ (Note3)	—	0.85	1.2	V

Note3: Pulse test

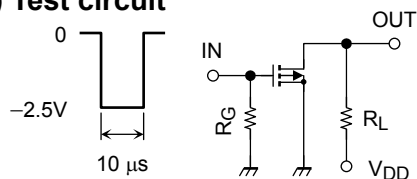
Unit: mm



Weight: 6.6 mg (typ.)

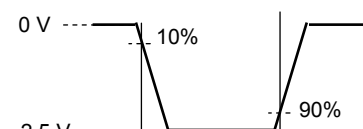
Switching Time Test Circuit

(a) Test circuit

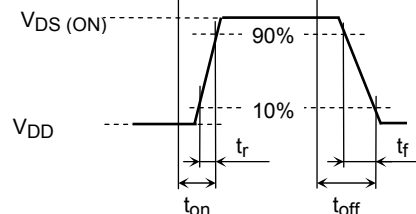


$V_{DD} = -10\text{ V}$
 $R_G = 4.7\ \Omega$
 $D.U. \leq 1\%$
 V_{IN} : $t_r, t_f < 5\text{ ns}$
 Common Source
 $T_a = 25^\circ\text{C}$

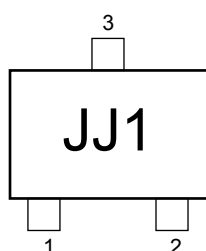
(b) V_{IN}



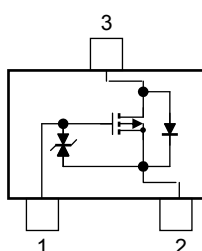
(c) V_{OUT}



Marking



Equivalent Circuit (top view)



Precaution

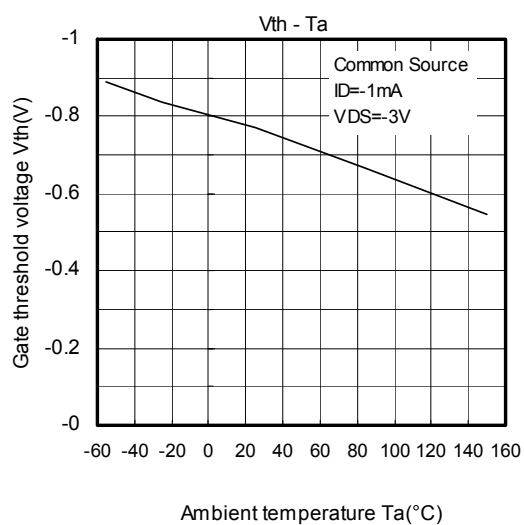
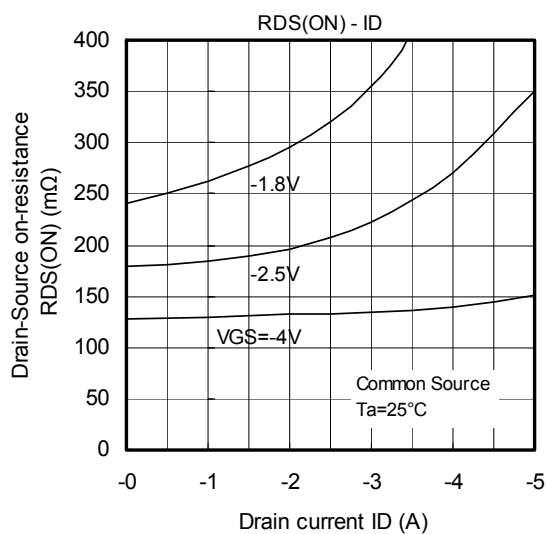
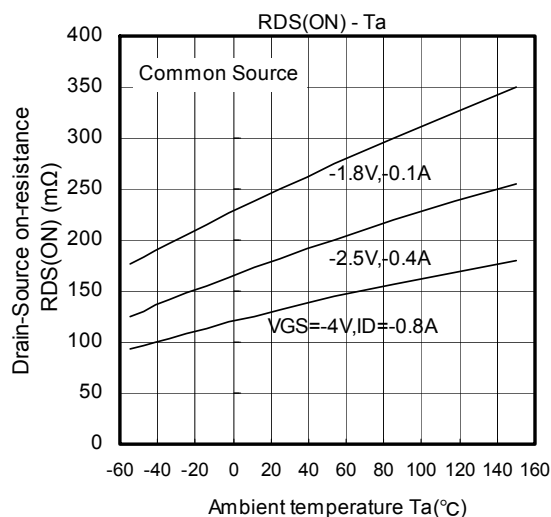
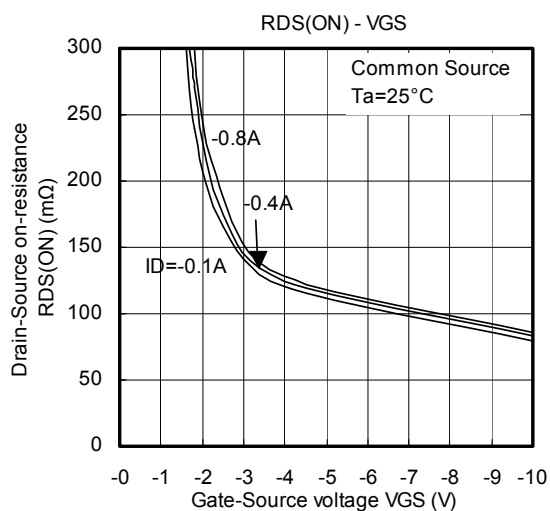
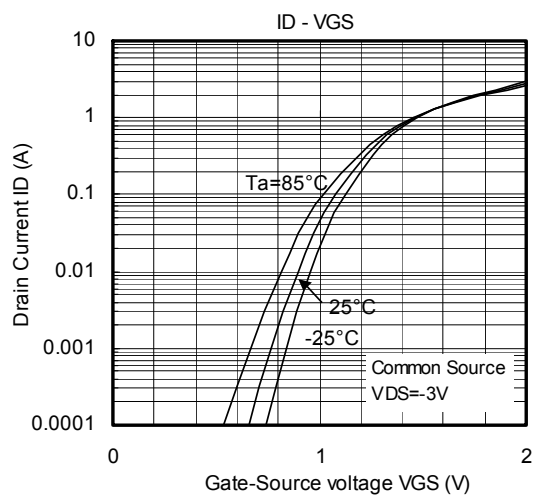
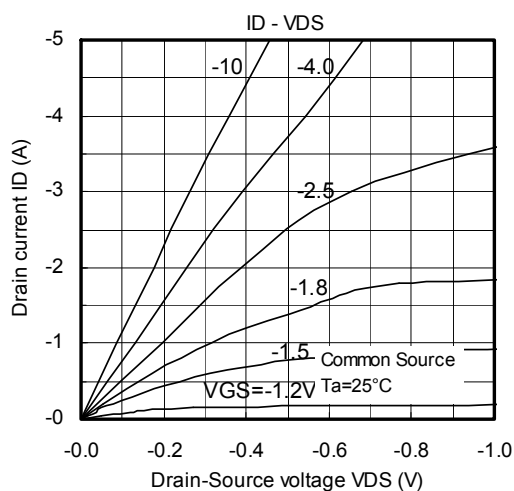
V_{th} can be expressed as the voltage between gate and source when the low operating current value is $I_D = -1\text{ mA}$ for this product. For normal switching operation, $V_{GS(ON)}$ requires a higher voltage than V_{th} , and $V_{GS(OFF)}$ requires a lower voltage than V_{th} .

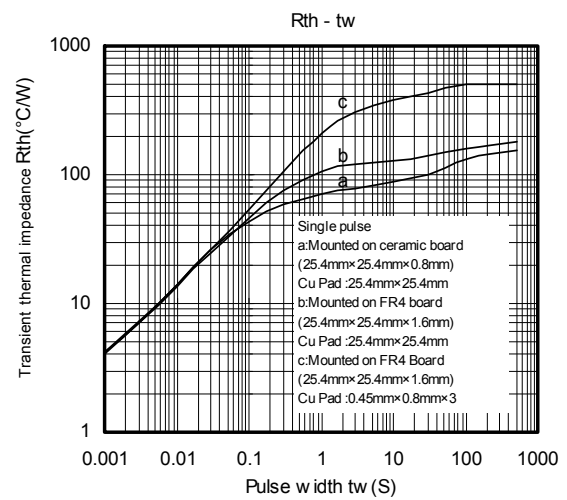
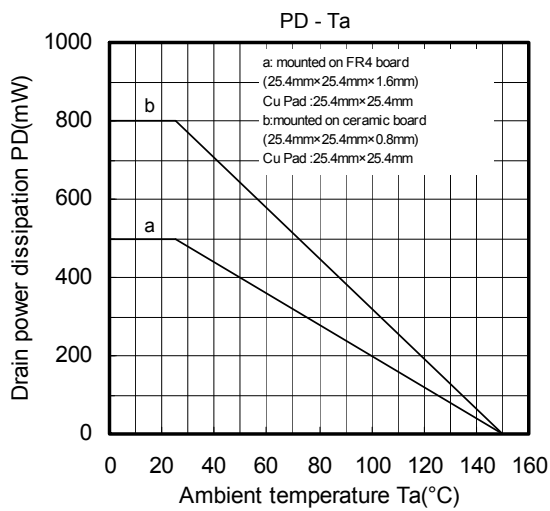
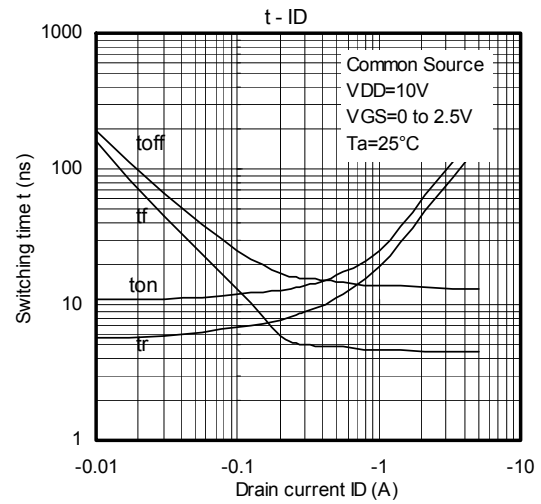
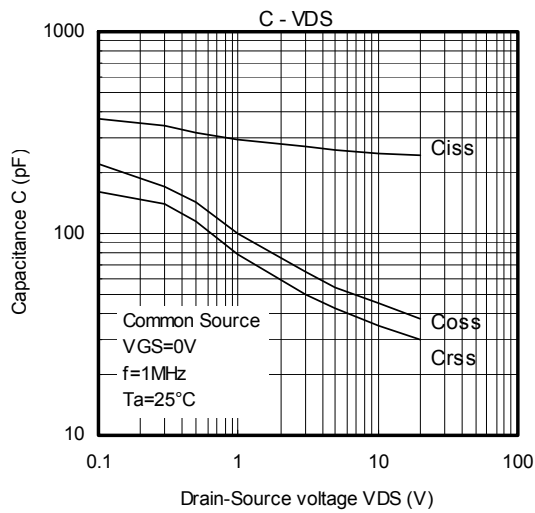
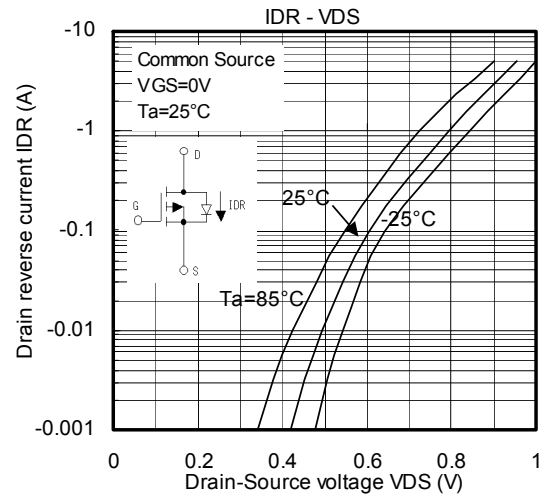
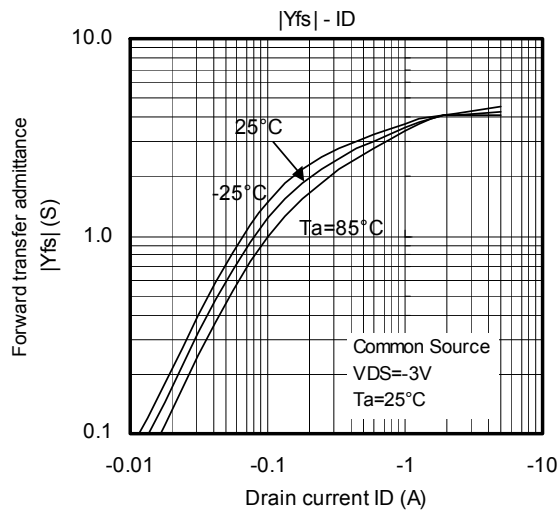
(The relationship can be established as follows: $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$)

Take this into consideration when using the device.

Handling Precaution

When handling individual devices which are not yet mounted on a circuit board, be sure that the environment is protected against electrostatic discharge. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.





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20070701-EN GENERAL

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